**Product data sheet** 

# 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Very fast switching
- Enhanced power dissipation capability of 1400 mW
- ElectroStatic Discharge (ESD) protection > 1 kV HBM

# 3. Applications

- LED driver
- Power management
- Low-side loadswitch
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

| Symbol                 | Parameter                        | Conditions   |     | Min | Тур | Max | Unit |
|------------------------|----------------------------------|--|-----|-----|-----|-----|------|
| $V_{DS}$               | drain-source voltage             | T <sub>j</sub> = 25 °C   |     | -   | -   | 20  | V    |
| V <sub>GS</sub>        | gate-source voltage              |  |     | -12 | -   | 12  | V    |
| I <sub>D</sub>         | drain current                    | V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s         | [1] | -   | -   | 9.1 | Α    |
| Static characteristics |                                  |  |     |     |     |     |      |
| R <sub>DSon</sub>      | drain-source on-state resistance | $V_{GS} = 4.5 \text{ V}; I_D = 6.9 \text{ A}; T_j = 25 \text{ °C}$ |     | -   | 15  | 19  | mΩ   |

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



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# 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|--------------------|----------------|
| 1   | D      | drain       | <u> </u>           | D<br>I         |
| 2   | D      | drain       |                    |                |
| 3   | G      | gate        | 1 12 13            | G T            |
| 4   | S      | source      | TSOP6 (SOT457)     |                |
| 5   | D      | drain       |                    |                |
| 6   | D      | drain       |                    | S<br>017aaa255 |

# 6. Ordering information

Table 3. Ordering information

| Type number | Package |  |         |  |  |  |
|-------------|---------|--|---------|--|--|--|
|             | Name    | Description                                      | Version |  |  |  |
| PMN16XNE    | TSOP6   | plastic surface-mounted package (TSOP6); 6 leads | SOT457  |  |  |  |

# 7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PMN16XNE    | G7           |

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# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol                    | Parameter               | Conditions   |     | Min | Max  | Unit |
|---------------------------|-------------------------|--|-----|-----|------|------|
| V <sub>DS</sub>           | drain-source voltage    | T <sub>j</sub> = 25 °C   |     | -   | 20   | V    |
| $V_{GS}$                  | gate-source voltage     |  |     | -12 | 12   | V    |
| I <sub>D</sub>            | drain current           | $V_{GS} = 4.5 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}; t \le 5 \text{ s}$ | [1] | -   | 9.1  | Α    |
|                           |                         | V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C                          | [1] | -   | 6.9  | Α    |
|                           |                         | V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C                         | [1] | -   | 4.4  | Α    |
| I <sub>DM</sub>           | peak drain current      | $T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$                        |     | -   | 28   | Α    |
| P <sub>tot</sub> total po | total power dissipation | T <sub>amb</sub> = 25 °C   | [2] | -   | 550  | mW   |
|                           |                         |  | [1] | -   | 1.4  | W    |
|                           |                         | T <sub>sp</sub> = 25 °C  |     | -   | 6.25 | W    |
| Tj                        | junction temperature    |  |     | -55 | 150  | °C   |
| T <sub>amb</sub>          | ambient temperature     |  |     | -55 | 150  | °C   |
| T <sub>stg</sub>          | storage temperature     |  |     | -65 | 150  | °C   |
| Source-dra                | in diode                |  |     | 1   |      |      |
| Is                        | source current          | T <sub>amb</sub> = 25 °C   | [1] | -   | 1.3  | Α    |

- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

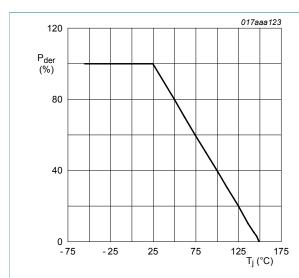


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

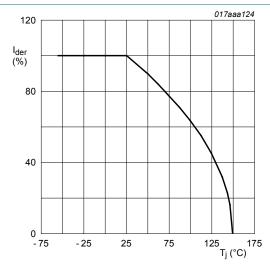


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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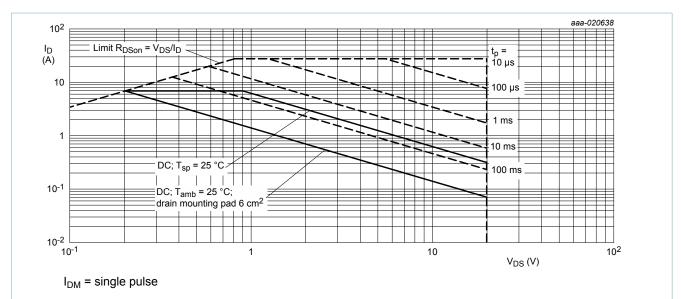


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

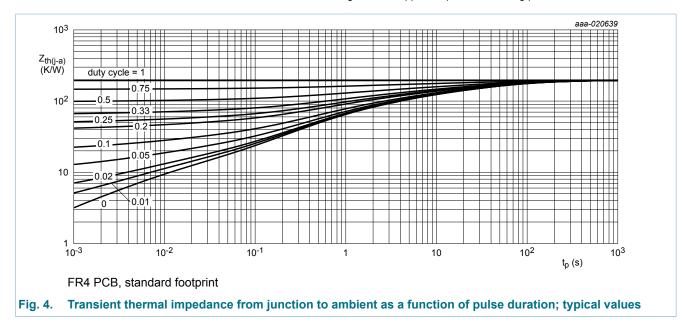
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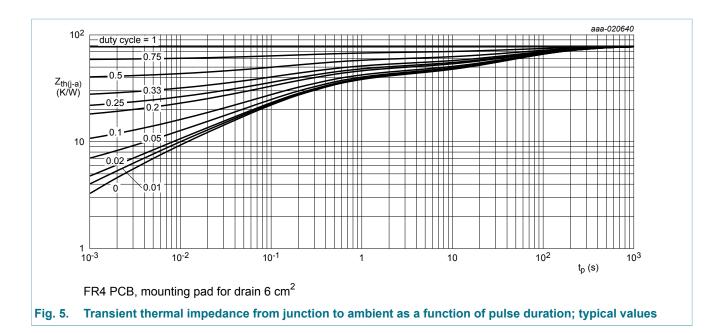
### 9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol   | Parameter  | Conditions           |     | Min | Тур | Max | Unit |
|--|--|----------------------|-----|-----|-----|-----|------|
| R <sub>th(j-a)</sub> thermal resistance from junction to ambient |  | in free air          | [1] | -   | 195 | 225 | K/W  |
|  |  | [2]                  | -   | 78  | 90  | K/W |      |
|  | ambient  | in free air; t ≤ 5 s | [2] | -   | 45  | 52  | K/W  |
| R <sub>th(j-sp)</sub>  | thermal resistance from junction to solder point |                      |     | -   | 15  | 20  | K/W  |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.





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# 10. Characteristics

Table 7. Characteristics

| Symbol              | Parameter   | Conditions   | Min | Тур  | Max  | Unit |
|---------------------|---|--|-----|------|------|------|
| Static cha          | racteristics  |  |     |      | '    | _    |
| $V_{(BR)DSS}$       | drain-source<br>breakdown voltage                                       | $I_D$ = 250 $\mu$ A; $V_{GS}$ = 0 V; $T_j$ = 25 °C                         | 20  | -    | -    | V    |
| $V_{GSth}$          | gate-source threshold voltage   | $I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$                    | 0.4 | 0.65 | 0.9  | V    |
| I <sub>DSS</sub>    | drain leakage current   | V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C      | -   | -    | 1    | μA   |
| I <sub>GSS</sub>    | gate leakage current  | V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C       | -   | -    | 10   | μA   |
|                     |   | $V_{GS}$ = -8 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C                             | -   | -    | -10  | μA   |
|                     |   | V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C     | -   | -    | 2    | μA   |
|                     |   | $V_{GS} = -4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$ | -   | -    | -2   | μA   |
|                     |   | $V_{GS}$ = 2.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C                            | -   | -    | 100  | nA   |
|                     |   | $V_{GS}$ = -2.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C                           | -   | -    | -100 | nA   |
| R <sub>DSon</sub>   | R <sub>DSon</sub> drain-source on-state resistance                      | $V_{GS}$ = 4.5 V; $I_{D}$ = 6.9 A; $T_{j}$ = 25 °C                         | -   | 15   | 19   | mΩ   |
|                     |   | $V_{GS}$ = 4.5 V; $I_{D}$ = 6.9 A; $T_{j}$ = 150 °C                        | -   | 23   | 29   | mΩ   |
|                     |   | $V_{GS}$ = 2.5 V; $I_D$ = 6.2 A; $T_j$ = 25 °C                             | -   | 19   | 24   | mΩ   |
|                     | V <sub>GS</sub> = 1.8 V; I <sub>D</sub> = 1.9 A; T <sub>j</sub> = 25 °C | -  | 22  | 30   | mΩ   |      |
|                     | $V_{GS}$ = 1.5 V; $I_D$ = 0.1 A; $T_j$ = 25 °C                          | -  | 30  | 70   | mΩ   |      |
| 9 <sub>fs</sub>     | forward transconductance  | $V_{DS} = 10 \text{ V}; I_D = 2 \text{ A}; T_j = 25 \text{ °C}$            | -   | 13   | -    | S    |
| $R_G$               | gate resistance   | f = 1 MHz; T <sub>j</sub> = 25 °C  | -   | 2.4  | -    | Ω    |
| Dynamic o           | characteristics   |  |     |      | '    |      |
| Q <sub>G(tot)</sub> | total gate charge   | $V_{DS}$ = 10 V; $I_{D}$ = 6 A; $V_{GS}$ = 4.5 V;                          | -   | 12   | 17   | nC   |
| $Q_{GS}$            | gate-source charge  | T <sub>j</sub> = 25 °C   | -   | 1.4  | -    | nC   |
| $Q_{GD}$            | gate-drain charge   |  | -   | 2.2  | -    | nC   |
| C <sub>iss</sub>    | input capacitance   | V <sub>DS</sub> = 10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;                  | -   | 1136 | -    | pF   |
| C <sub>oss</sub>    | output capacitance  | T <sub>j</sub> = 25 °C   | -   | 137  | -    | pF   |
| C <sub>rss</sub>    | reverse transfer capacitance  |  | -   | 112  | -    | pF   |
| t <sub>d(on)</sub>  | turn-on delay time  | $V_{DS}$ = 10 V; $I_{D}$ = 6 A; $V_{GS}$ = 4.5 V;                          | -   | 9    | -    | ns   |
| t <sub>r</sub>      | rise time   | $R_{G(ext)} = 6 \Omega$ ; $T_j = 25 °C$                                    | -   | 20   | -    | ns   |
| t <sub>d(off)</sub> | turn-off delay time   |  | -   | 31   | -    | ns   |
| t <sub>f</sub>      | fall time   |  | -   | 32   | -    | ns   |

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| Symbol          | Parameter            | Conditions   |  | Min | Тур | Max | Unit |
|-----------------|----------------------|--|--|-----|-----|-----|------|
| Source-drain o  | Source-drain diode   |  |  |     |     |     |      |
| V <sub>SD</sub> | source-drain voltage | $I_S = 1.3 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$ |  | -   | 0.7 | 1.2 | V    |

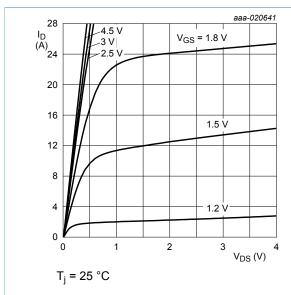


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

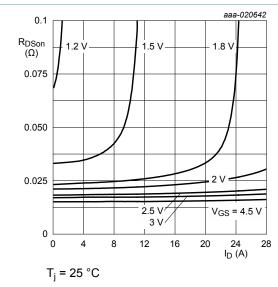
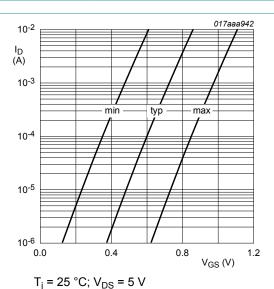
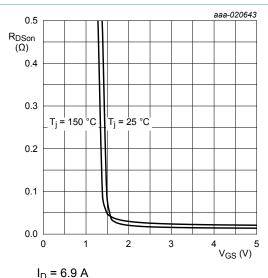


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values



1<sub>j</sub> = 23 0, v<sub>DS</sub> = 3 v

Fig. 7. Subthreshold drain current as a function of gate-source voltage



*D* 

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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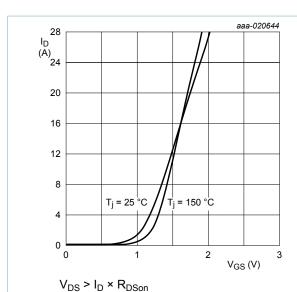


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

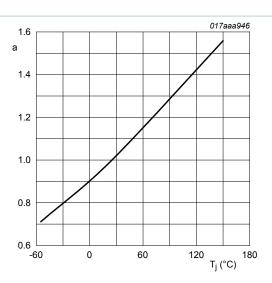


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

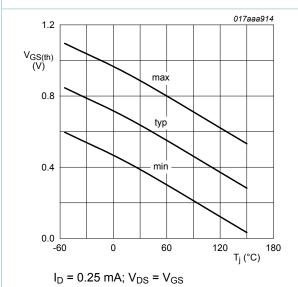


Fig. 12. Gate-source threshold voltage as a function of junction temperature

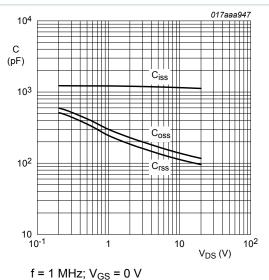


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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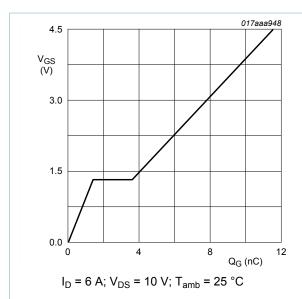


Fig. 14. Gate-source voltage as a function of gate charge; typical values

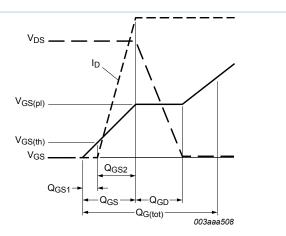


Fig. 15. MOSFET transistor: Gate charge waveform definitions

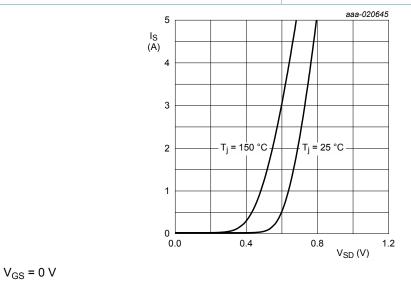
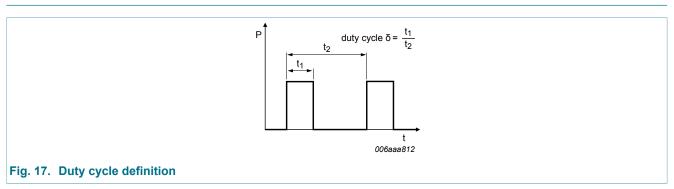


Fig. 16. Source current as a function of source-drain voltage; typical values

# 11. Test information

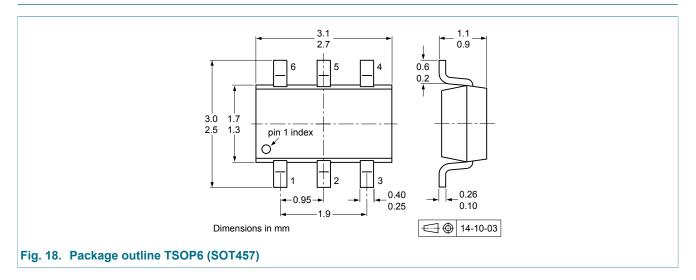


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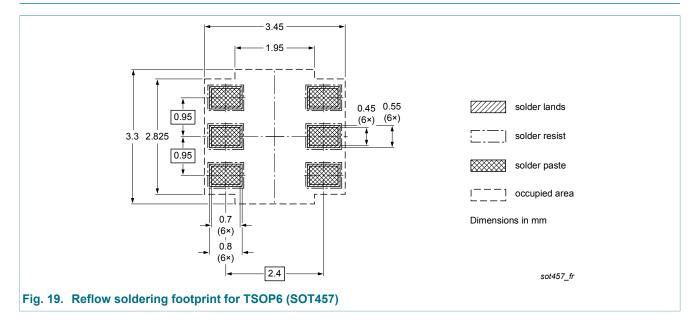
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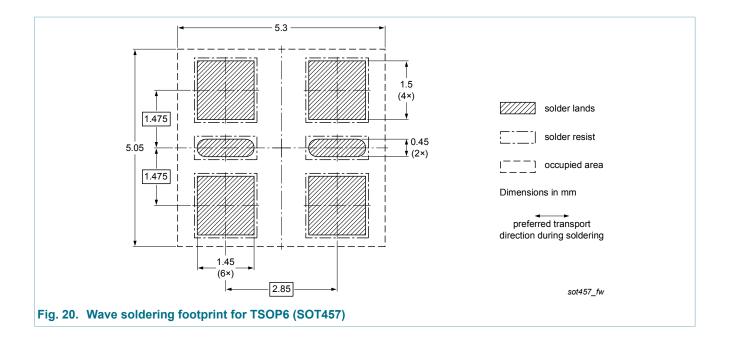
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# 12. Package outline



# 13. Soldering





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# 14. Revision history

### Table 8. Revision history

| Data sheet ID | Release date | Data sheet status  | Change notice | Supersedes |
|---------------|--------------|--------------------|---------------|------------|
| PMN16XNE v.1  | 20160129     | Product data sheet | -             | -          |

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## 15. Legal information

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